

HAT1035R

Silicon P Channel Power MOS FET
High Speed Power Switching

REJ03G0845-0100

Rev.1.00

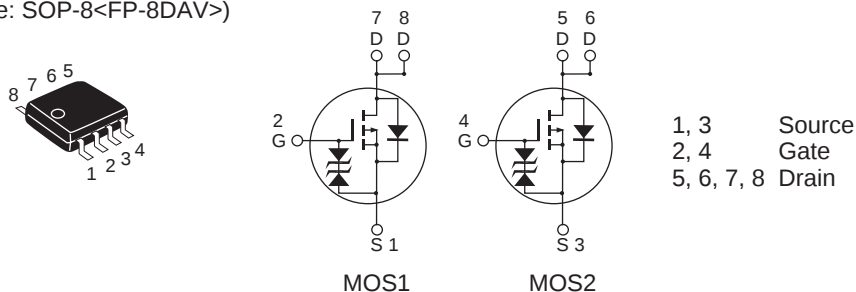
Apr.22,2005

Features

- Low on-resistance
- Capable of -4 V gate drive
- Low drive current
- High density mounting

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8<FP-8DAV>)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source voltage	V_{DSS}	-150	V
Gate to Source voltage	V_{GSS}	±15	V
Drain current	I_D	-0.25	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-1	A
Body-Drain diode reverse Drain current	I_{DR}	-0.25	A
Channel dissipation	P_{ch} ^{Note2}	1	W
Channel dissipation	P_{ch} ^{Note3}	1.5	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$

2. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm)

3. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm)

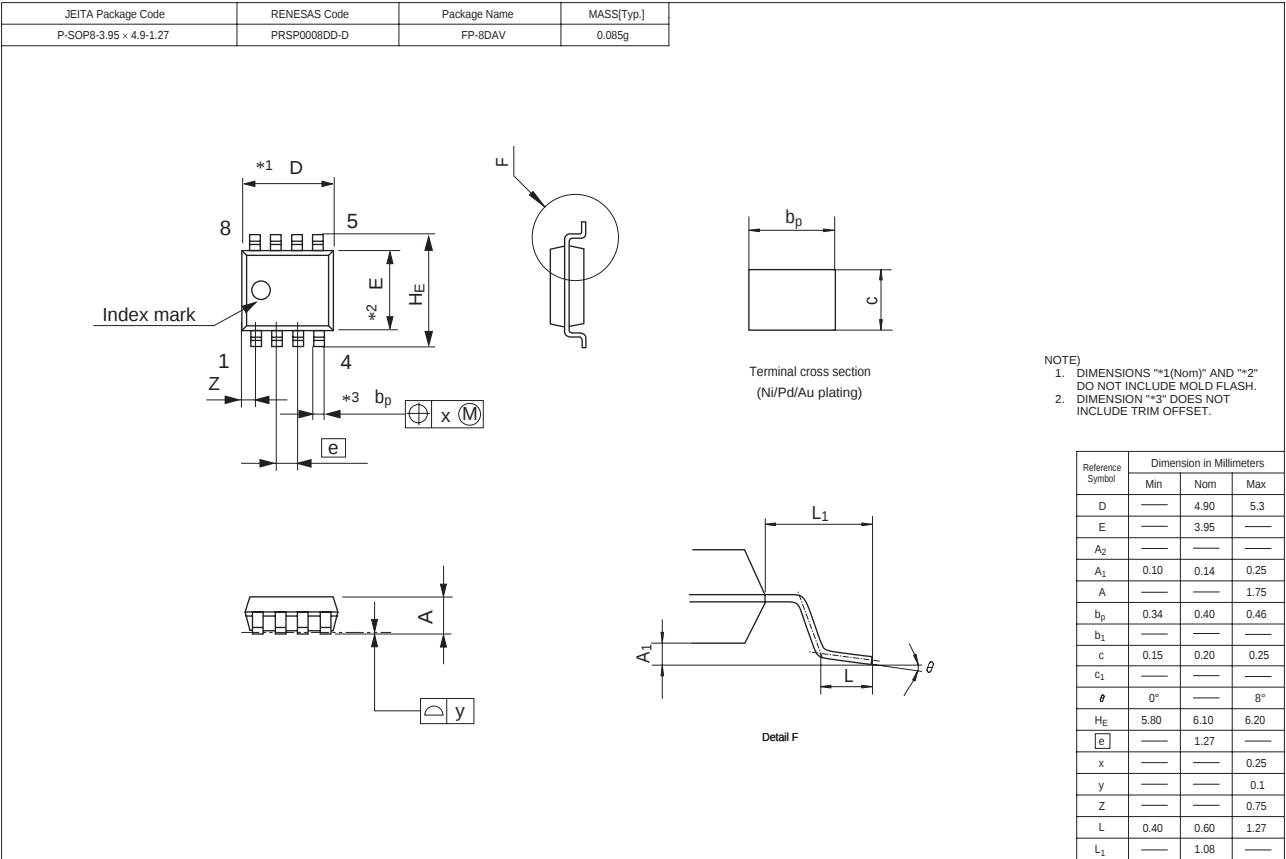
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	-150	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to Source breakdown voltage	$V_{(BR)GSS}$	± 15	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to Source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 12 \text{ V}$, $V_{DS} = 0$
Zero Gate voltage Drain current	I_{DSS}	—	—	-5	μA	$V_{DS} = -150 \text{ V}$, $V_{GS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$V_{DS} = -10 \text{ V}$, $I_D = -1 \text{ mA}$
Static Drain to Source on state resistance	$R_{DS(on)}$	—	5.0	6.2	Ω	$I_D = -0.25 \text{ A}$, $V_{GS} = -10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	6.0	7.5	Ω	$I_D = -0.25 \text{ A}$, $V_{GS} = -4 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	7.0	10.0	Ω	$I_D = -1 \text{ A}$, $V_{GS} = -5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	0.29	0.45	—	S	$I_D = -0.25 \text{ A}$, $V_{DS} = -10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	92	—	pF	$V_{DS} = -10 \text{ V}$ $V_{GS} = 0$ $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	37	—	pF	
Reverse transfer capacitance	C_{rss}	—	10	—	pF	
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$V_{GS} = -5 \text{ V}$, $I_D = -0.25 \text{ A}$, $V_{DD} \cong -30 \text{ V}$
Rise time	t_r	—	13	—	ns	
Turn-off delay time	$t_{d(off)}$	—	22	—	ns	
Fall time	t_f	—	15	—	ns	
Body-Drain diode forward voltage	V_{DF}	—	-0.9	-1.4	V	$I_F = -0.25 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-Drain diode reverse recovery time	t_{rr}	—	80	—	ns	$I_F = -0.25 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT1035R-EL-E	2500 pcs.	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001